

**16 AMPERES  
COMPLEMENTARY SILICON-  
POWER TRANSISTORS  
250 VOLTS, 250 WATTS**

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**MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CEO}$	250	Vdc
Collector-Base Voltage	$V_{CBO}$	400	Vdc
Emitter-Base Voltage	$V_{EBO}$	5	Vdc
Collector-Emitter Voltage – 1.5V	$V_{CEX}$	400	Vdc
Collector Current – Continuous	$I_C$	16	Adc
Collector Current – Peak (Note 1)	$I_{CM}$	30	Adc
Base Current – Continuous	$I_B$	5	Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	250 1.43	W W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	-65 to +200	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Pulse Test: Pulse Width = 5  $\mu\text{s}$ , Duty Cycle 10%.

**THERMAL CHARACTERISTICS**

Characteristics	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.7	$^\circ\text{C}/\text{W}$



**TO-204AA (TO-3)  
CASE 1-07  
STYLE 1**

**MARKING DIAGRAM**



MJ2119x = Device Code  
          x = 5 or 6  
G = Pb-Free Package  
A = Assembly Location  
Y = Year  
WW = Work Week  
MEX = Country of Origin

**ORDERING INFORMATION**

Device	Package	Shipping
MJ21195G	TO-204 (Pb-Free)	100 Units / Tray
MJ21196G	TO-204 (Pb-Free)	100 Units / Tray

\*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

**MJ21195G – PNP      MJ21196G – NPN**







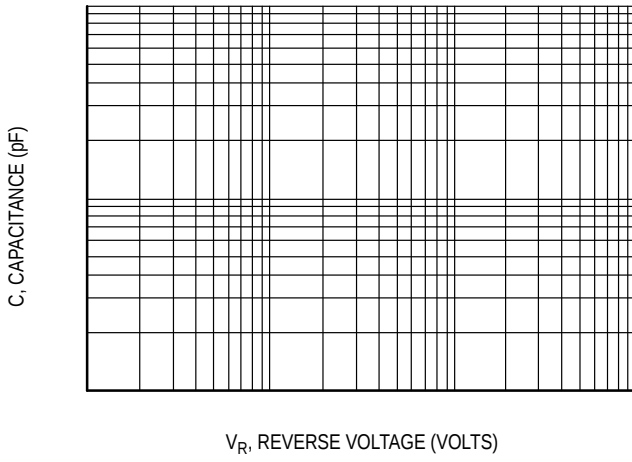


Figure 14. MJ21195 Typical Capacitance

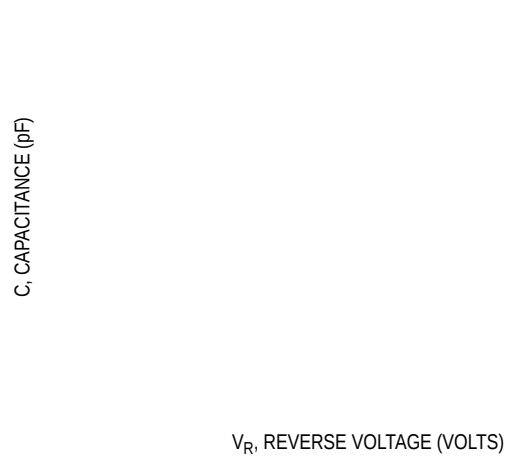
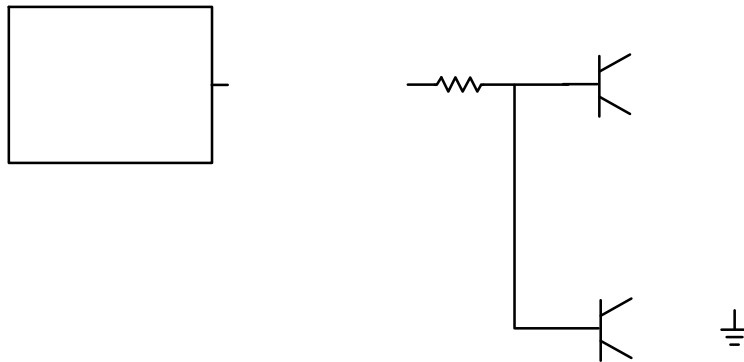
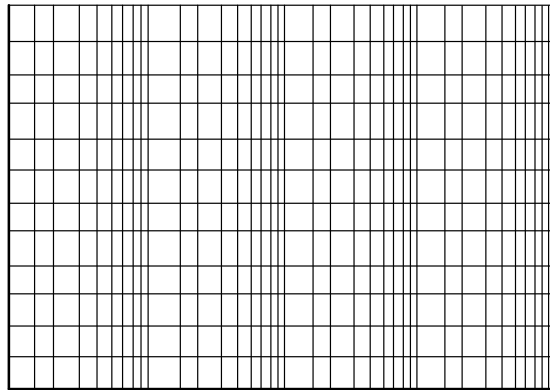
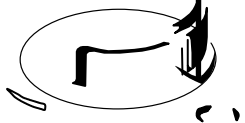


Figure 15. MJ21196 Typical Capacitance



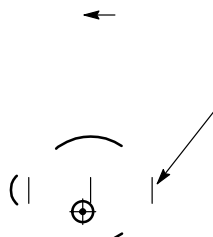
E6: 1. A E 2. E E CASE: C EC	E7: 1. A DE 2. E CASE: CA DE	E8: 1. CA DE #1 2. CA DE #2 CASE: A DE	E9: 1. A DE #1 2. A DE #2 CASE: CA DE
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TO-204 (TO-3)



S A 1:1

E8  
 1. D E A D E A C E A  
 14.5, 1982.  
 2. C D E : C  
 3. A E S A D E S A S CA ED  
 E F E E CED -204AA E S A



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